

# **PQMB11Z Datasheet**



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DiGi Electronics Part Number PQMB11Z-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PQMB11Z

Description TRANS PREBIAS 2PNP DFN1010B-6

Detailed Description Pre-Biased Bipolar Transistor (BJT) 2 PNP - Pre-Bias ed (Dual) 50V 100mA 180MHz 230mW Surface Mou

nt DFN1010B-6



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# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
PQMB11Z	Nexperia USA Inc.
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
2 PNP - Pre-Biased (Dual)	100mA
Voltage - Collector Emitter Breakdown (Max):	Resistor - Base (R1):
50V	10kOhms
Resistor - Emitter Base (R2):	DC Current Gain (hFE) (Min) @ Ic, Vce:
10kOhms	30 @ 5mA, 5V
Vce Saturation (Max) @ lb, lc:	Current - Collector Cutoff (Max):
Vce Saturation (Max) @ lb, lc: 150mV @ 500μA, 10mA	Current - Collector Cutoff (Max): 1µA
150mV @ 500μA, 10mA	1μΑ
150mV @ 500μA, 10mA Frequency - Transition:	1μA Power - Max:
150mV @ 500μA, 10mA Frequency - Transition: 180MHz	1μA Power - Max: 230mW
150mV @ 500μA, 10mA  Frequency - Transition:  180MHz  Grade:	1μA Power - Max: 230mW Qualification:
150mV @ 500μA, 10mA  Frequency - Transition:  180MHz  Grade:  Automotive	1μA Power - Max: 230mW Qualification: AEC-Q101
150mV @ 500μA, 10mA  Frequency - Transition:  180MHz  Grade:  Automotive  Mounting Type:	1μA Power - Max: 230mW Qualification: AEC-Q101 Package / Case:

# **Environmental & Export classification**

8541.21.0075

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



# PQMB11

# PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$

**26 October 2015** 

**Product data sheet** 

### 1. General description

PNP/PNP Resistor-Equipped Transistors (RET) in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PQMH11.

NPN/PNP complement: PQMD3.

#### 2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Low package height of 0.37 mm
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

## 3. Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications
- Mobile applications

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	Per transistor						
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	-50	V
Io	output current			-	-	-100	mA
Per transistor	Per transistor						,
R1	bias resistor 1	T <sub>amb</sub> = 25 °C	[1]	7	10	13	kΩ
R2/R1	bias resistor ratio		[1]	0.8	1	1.2	

[1] See section "Test information" for resistor calculation and test conditions.



PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$ 

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1	5 7 7	O1 I2 GND2
2	I1	input ( base) TR1	$\begin{bmatrix} 1 \\ 7 \end{bmatrix} \begin{bmatrix} 6 \\ 6 \end{bmatrix}$	
3	O2	output (collector) TR2	2 5	R1 R2
4	GND2	GND (emitter) TR2	8 5	TR1 TR2
5	12	input ( base) TR2	3 4	R2 R1
6	01	output (collector) TR1	Transparent top view	
7	01	output (collector) TR1	DFN1010B-6 (SOT1216)	GND1 I1 O2 aaa-019790
8	O2	output (collector) TR2		ada 075750

# 6. Ordering information

Table 3. Ordering information

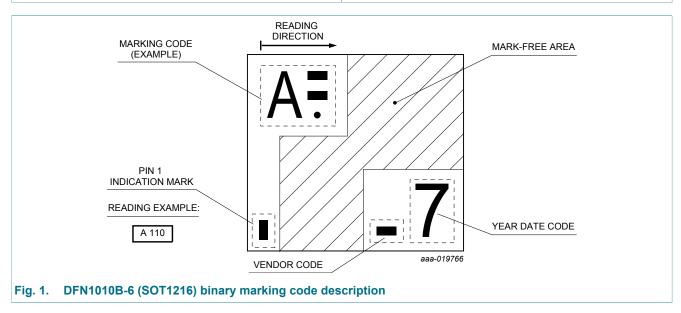
Type number	Package		
	Name	Description	Version
PQMB11	DFN1010B-6	DFN1010B-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1216

PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$ 

# 7. Marking

Table 4. Marking codes

Type number	Marking code
PQMB11	A 110



PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$ 

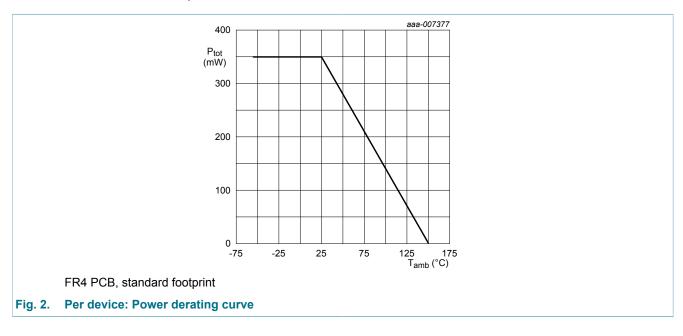
# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor	'	'			
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-50	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-10	V
VI	input voltage	positive		-	10	V
		negative		-	-40	V
I <sub>O</sub>	output current			-	-100	mA
I <sub>CM</sub>	peak collector current			-	-100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	230	mW
Per device	<u> </u>		,		'	
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	350	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



#### PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$

#### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	543	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	357	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

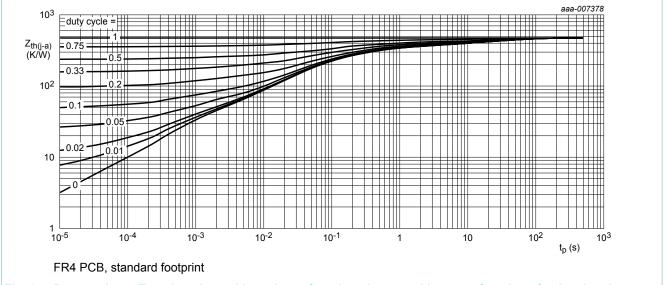


Fig. 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

#### PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$

### 10. Characteristics

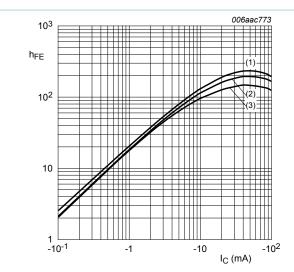
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
I <sub>CBO</sub>	collector-base cut-off current (emitter open)	V <sub>CB</sub> = -50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	-100	nA
I <sub>CEO</sub>	collector-emitter cut-off	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	-1	μA
	current (base open)	V <sub>CE</sub> = -30 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 150 °C		-	-	-5	μA
I <sub>EBO</sub>	emitter-base cut-off current (collector open)	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	-400	μA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -5 V; $I_{C}$ = -5 mA; $T_{amb}$ = 25 °C		30	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = -10 mA; $I_B$ = -0.5 mA; $T_{amb}$ = 25 °C		-	-	-150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE}$ = -5 V; $I_{C}$ = -100 $\mu$ A; $T_{amb}$ = 25 °C		-	-1.1	-0.8	V
$V_{I(on)}$	on-state input voltage	$V_{CE}$ = -0.3 V; $I_{C}$ = -10 mA; $T_{amb}$ = 25 °C		-2.5	-1.8	-	V
R1	bias resistor 1	T <sub>amb</sub> = 25 °C	[1]	7	10	13	kΩ
R2/R1	bias resistor ratio		[1]	0.8	1	1.2	
C <sub>C</sub>	collector capacitance	$V_{CB}$ = -10 V; $I_{E}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C		-	-	3	pF
f <sub>T</sub>	transition frequency	$V_{CE}$ = -5 V; $I_{C}$ = -10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	[2]	-	180	-	MHz

<sup>[1]</sup> See section "Test information" for resistor calculation and test conditions.

<sup>[2]</sup> Characteristics of built-in transistor

#### PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$



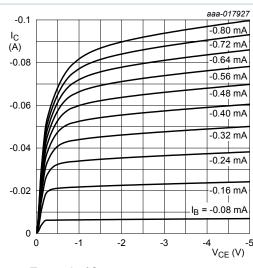
$$V_{CE} = -5 V$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

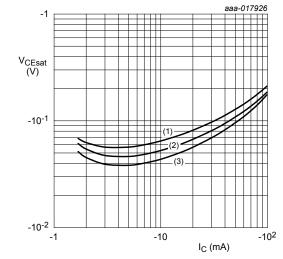
(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 4. DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$ 

Fig. 5. Collector current as a function of collectoremitter voltage; typical values



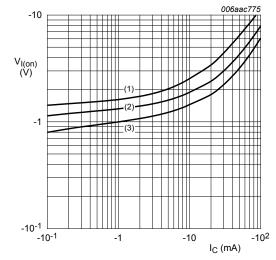
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 6. Collector-emitter saturation voltage as a function of collector current; typical values



$$V_{CE} = -0.3 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

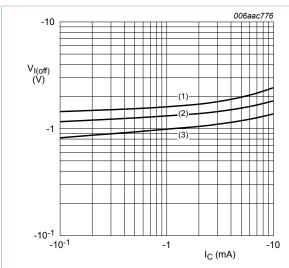
(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. On-state input voltage as a function of collector current; typical values

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#### PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$



$$V_{CF} = -5 V$$

Fig. 8.

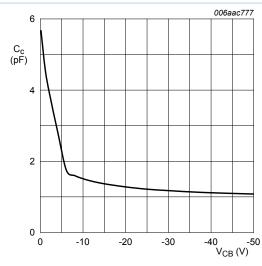
(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3)  $T_{amb}$  = 100 °C

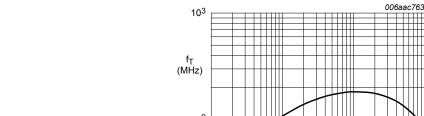
current; typical values

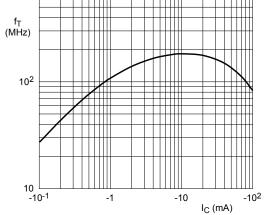
Off-state input voltage as a function of collector



 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$ 

Collector capacitance as a function of collector-Fig. 9. base voltage; typical values





 $V_{CE}$  = -5 V;  $T_{amb}$  = 25 °C

Fig. 10. Transition frequency as a function of collector current; typical values of built-in transistor

#### 11. Test information

#### 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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PQMB11Z Nexperia USA Inc. TRANS PREBIAS 2PNP DFN1010B-6

#### PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$

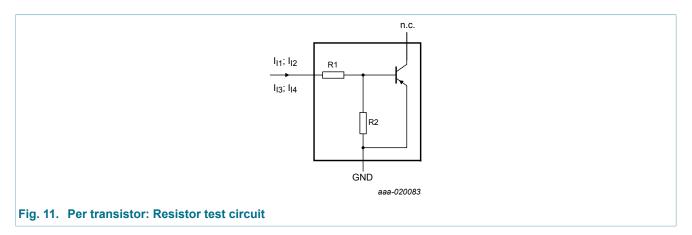
#### 11.2 Resistor calculation

Calculation of bias resistor 1 (R1)

$$RI = \frac{V(I_{12}) - V(I_{11})}{I_{12} - I_{11}}$$

Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$

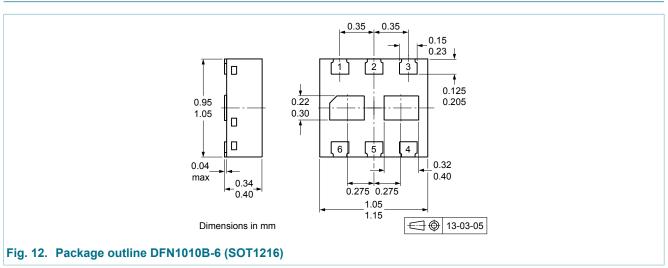


#### 11.3 Resistor test conditions

Table 8. Resistor test conditions

R1 (kΩ)	R2 (kΩ)	Test conditions			
		I <sub>I1</sub>	I <sub>I2</sub>	I <sub>I3</sub>	I <sub>14</sub>
10	10	-350 μΑ	-450 μΑ	350 μΑ	450 μΑ

### 12. Package outline



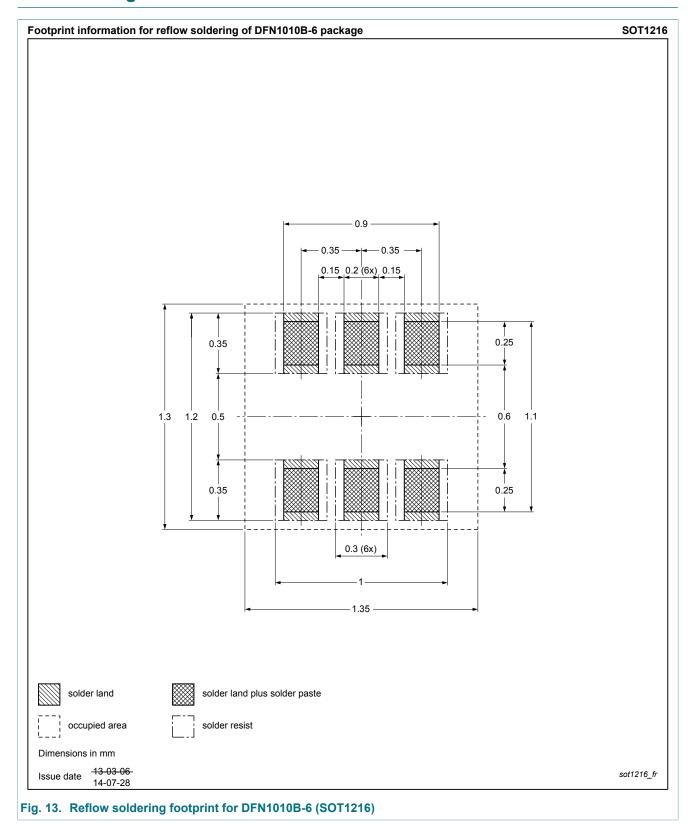
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PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$ 

# 13. Soldering



PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$ 

# 14. Revision history

#### Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PQMB11 v.1	20151026	Product data sheet	-	-

#### PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$

#### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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#### PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$

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### PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$

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